

## **Amendments to the Claims**

Claims 1-8 (Cancelled).

9. (Currently amended) A method of forming a transistor structure, comprising:

forming a transistor gate over a substrate, the transistor gate comprising a sidewall which comprises electrically conductive material;

forming an electrically insulative material along the electrically conductive material of the transistor gate sidewall; the electrically insulative material comprising at least two separate layers; a first of the at least two layers comprising  $Al_pO_q$ , wherein p and q are greater than 0 and less than 10; a second of the at least two layers consisting essentially of silicon and nitrogen, the first of the at least two layers being disposed between the transistor gate sidewall and the second of the at least two layers;

anisotropically etching the electrically insulative material to form a spacer along the transistor gate sidewall; the anisotropically etching comprising etching both of the first and second of the at least two layers;

depositing a dopant barrier layer over the spacer; and

forming a doped oxide layer over the barrier layer; and

etching a contact opening through the doped oxide and through the barrier layer adjacent the spacer utilizing the spacer to align the contact opening, the etching exposing at least a portion of the spacer.

10. (Original) The method of claim 9 further comprising implanting a dopant into the substrate and utilizing the spacer to align the dopant during the implant.

Claims 11-12 (Cancelled).

13. (Previously presented) The method of claim 9 wherein the first of the at least two layers consists essentially of  $\text{Al}_p\text{O}_q$ .

Claims 14-31 (Cancelled).

32. (Previously presented) The method of claim 9 wherein the first of the at least two layers consists of  $\text{Al}_p\text{O}_q$ .

33. (Previously presented) The method of claim 9 wherein the first of the at least two layers consists of  $\text{Al}_2\text{O}_3$ .

34. (Previously presented) The method of claim 9 wherein the dopant barrier layer comprises silicon dioxide.

35. (Previously presented) The method of claim 9 wherein the doped oxide layer comprises BPSG.

36. (New) The method of claim 9 further comprising depositing a conductive material within the contact opening, a portion of the conductive material being in contact with the first of the at least two layers comprised by the sidewall.